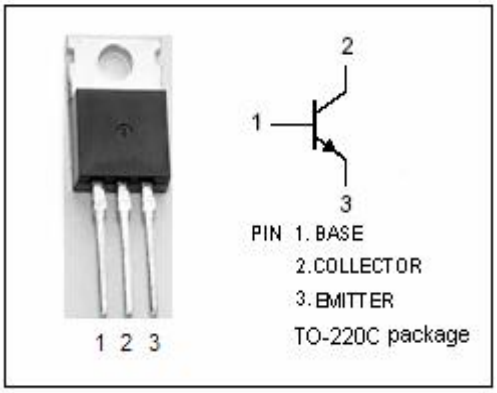
isc Silicon NPN Power Transistor — 2SC1755



DESCRIPTION

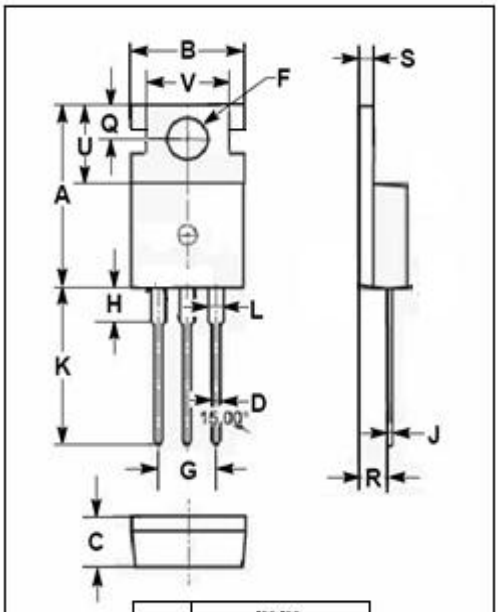
- High Collector-Emitter Breakdown Voltage-
  :$V_{(BR)CEO}$= 300V(Min)
- DC Current Gain-
  : h_{FE}= 40-200 @I_C= 10mA, V_{CE}= 10V
- High Current-Gain Bandwidth Product
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for color TV chroma, video , audio output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	200	mA
I_{CM}	Collector Current-Peak	700	mA
P_C	Collector Power Dissipation @ T_a=25℃	1.2	W
	Collector Power Dissipation @ T_C=25℃	15	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-40~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon NPN Power Transistor 2SC1755

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 50mA; I_B= 5mA			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 200V ; I_E= 0			0.1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	μA
h_{FE}	DC Current Gain	I_C= 10mA ; V_{CE}= 10V	40		200	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 50V; f_{test}= 1MHz			5.3	pF
f_T	Current-Gain—Bandwidth Product	I_C= 10mA; V_{CE}= 30V	50			MHz

◆ **h_{FE} Classifications**

C	D	E
40-80	60-120	100-200